1. General description

NPN/PNP general-purpose double transistors in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847RA PNP/PNP complement: BC857RA

2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- · General-purpose switching and amplification
- · Mobile applications

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|------------------|---|---|--|-----|-----|-----|------|--|
| Per transistor; | Per transistor; for the PNP transistor with negative polarity | | | | | | | |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 45 | V | |
| I _C | collector current | | | - | - | 100 | mA | |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | - | 200 | mA | |
| h _{FE} | DC current gain | V_{CE} = 5 V; I_{C} = 2 mA; T_{amb} = 25 °C | | 200 | - | 450 | | |



45 V, 100 mA NPN/PNP general-purpose double transistors

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|---------------|------------------------|---|
| 1 | E1 | emitter TR1 | | 6 5 4 |
| 2 | B1 | base TR1 | 7 6 | |
| 3 | C2 | collector TR2 | 2 5 | $\left(\begin{array}{c} TR1 \end{array}\right)$ |
| 4 | E2 | emitter TR2 | | |
| 5 | B2 | base TR2 | 3 8 4 | 1 2 3 |
| 6 | C1 | collector TR1 | | sym019 |
| 7 | C1 | collector TR1 | Transparent top view | |
| 8 | C2 | collector TR2 | DFN1412-6 (SOT1268) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|---------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| BC847RAPN | | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm | SOT1268 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BC847RAPN | A4 |

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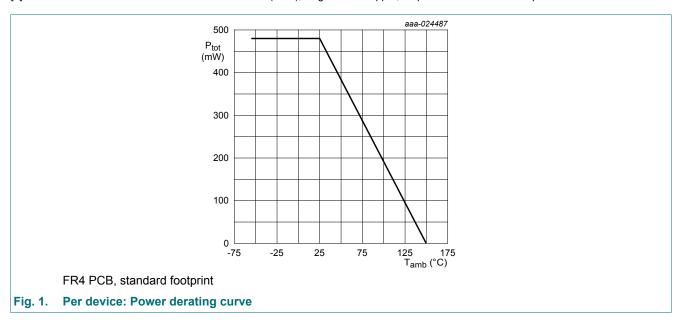
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|--------------------------------|-------------------------------------|-----|-----|-----|------|
| Per transist | or; for the PNP transistor wit | h negative polarity | , | ' | | |
| V _{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | | - | 45 | V |
| V_{EBO} | emitter-base voltage | open collector | | - | 6 | V |
| I _C | collector current | | | - | 100 | mA |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | 200 | mA |
| I _{BM} | peak base current | | | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 325 | mW |
| Per device | | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 480 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------|---|-------------|-----|-----|-----|-----|------|
| Per transistor | | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 385 | K/W |
| Per device | | | | | | | , |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 261 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

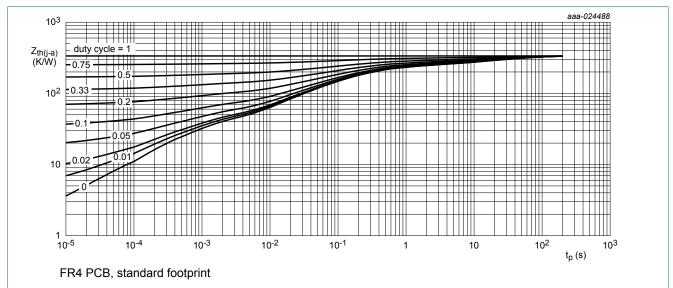


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 100 mA NPN/PNP general-purpose double transistors

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Mir | 1 Тур | Max | Unit |
|--------------------|------------------------------|---|-----|-------|-----|------|
| Per transist | or; for the PNP transistor v | with negative polarity | | | | |
| I _{CBO} | collector-base cut-off | V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 15 | nA |
| | current | V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C | - | - | 5 | μΑ |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C | 200 |) - | 450 | |
| V _{CEsat} | collector-emitter | I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C | - | - | 100 | mV |
| saturation | saturation voltage | I_C = 100 mA; I_B = 5 mA; T_{amb} = 25 °C | - | - | 300 | mV |
| V _{BEsat} | base-emitter saturation | I _C = 10 mA; I _B = 0.5 mA; T _{amb} = 25 °C | - | 760 | - | mV |
| | voltage | I_C = 100 mA; I_B = 5 mA; T_{amb} = 25 °C | - | 900 | - | mV |
| V _{BE} | base-emitter voltage | V _{CE} = 5 V; I _C = 2 mA; T _{amb} = 25 °C | 600 | 660 | 725 | mV |
| | | V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C | - | 710 | 820 | mV |
| C _c | collector capacitance | $V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$ | - | - | 4 | pF |
| C _e | emitter capacitance | $V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ | - | 11 | - | pF |
| | | V_{EB} = -0.5 V; I_{C} = 0 mA; i_{c} = 0 mA; f = 1 MHz; T_{amb} = 25 °C | - | 10 | - | pF |
| f _T | transition frequency | V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C | 100 |) - | - | MHz |
| NF | noise figure | V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 MHz; T_{amb} = 25 °C | - | - | 10 | dB |

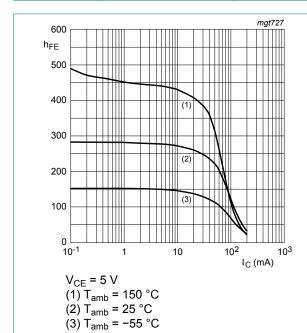


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

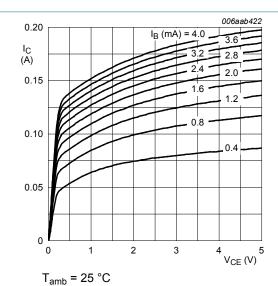
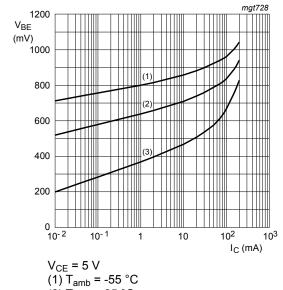


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

BC847RAPN

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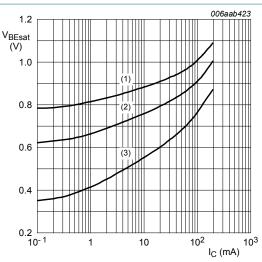
(1)
$$I_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3) $T_{amb} = 150 \,^{\circ}\text{C}$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 5. NPN transistor: Base-emitter voltage as a function of collector current; typical values



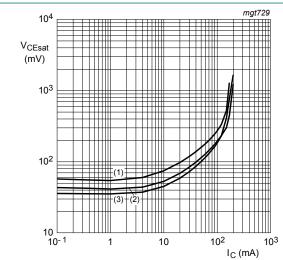
$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = -55 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = -55 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = 150 \,^{\circ}C$

Fig. 6. NPN transistor: Base-emitter saturation voltage as a function of collector current; typical values



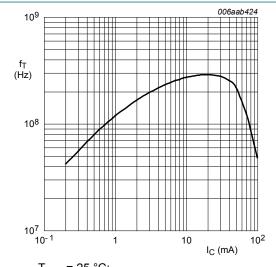
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

NPN transistor: Collector-emitter saturation Fig. 7. voltage as a function of collector current; typical values

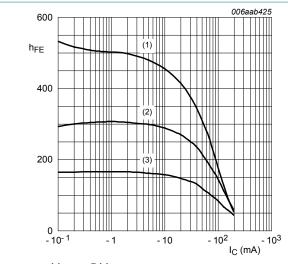


$$T_{amb}$$
 = 25 °C;
 V_{CE} = 5 V;

f = 100 MHz

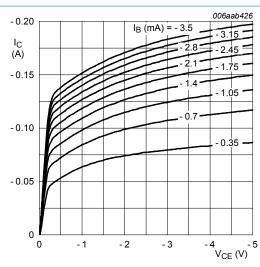
NPN transistor: Transition frequency as a Fig. 8. function of collector current; typical values

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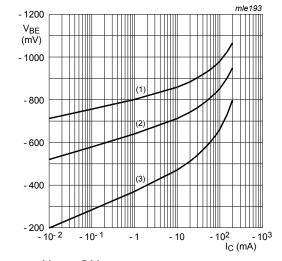
$$V_{CE}$$
 = -5 V

PNP transistor: DC current gain as a function of Fig. 9. collector current; typical values



 T_{amb} = 25 °C

Fig. 10. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



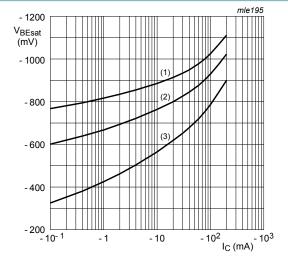
 V_{CE} = -5 V

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 11. PNP transistor: Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 12. PNP transistor: Base-emitter saturation voltage as a function of collector current; typical values

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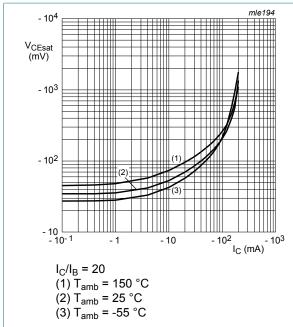


Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

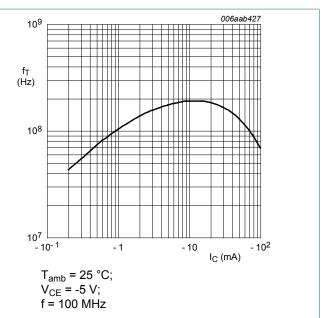


Fig. 14. PNP transistor: Transition frequency as a function of collector current; typical values

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

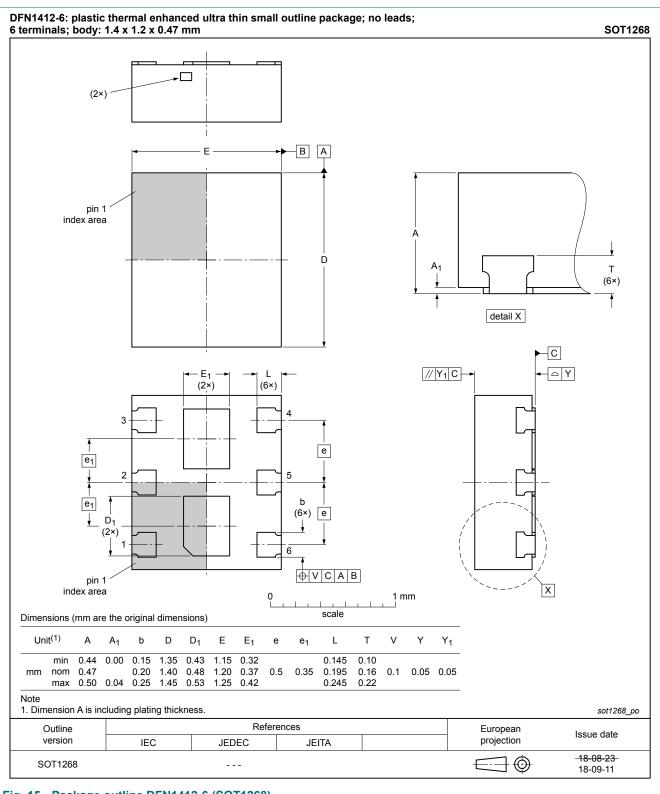
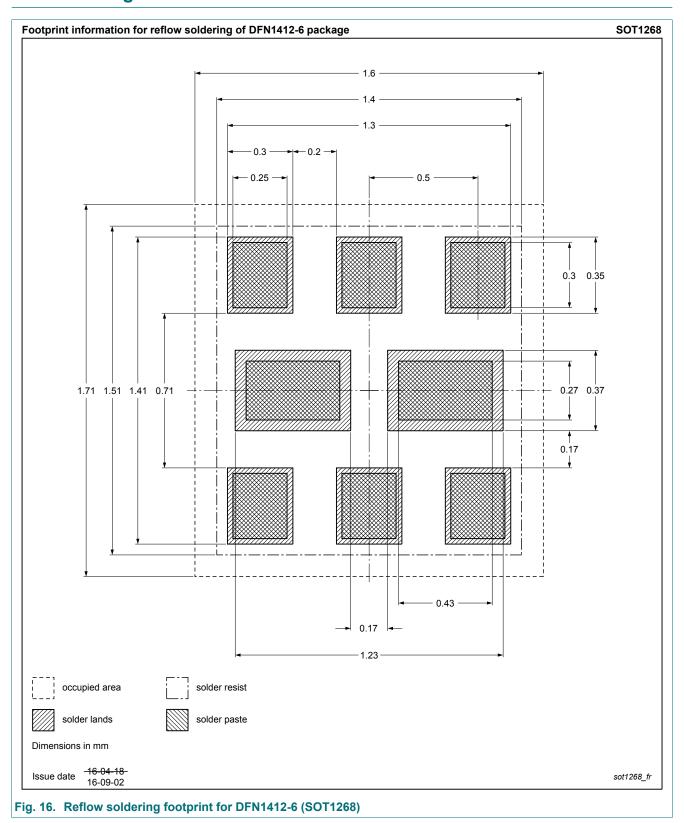


Fig. 15. Package outline DFN1412-6 (SOT1268)

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13. Soldering



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14. Revision history

Table 8. Revision history

| - Laboration in the contract of the contract o | | | | | | | | |
|--|----------------------|---|---------------|---------------|--|--|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | | |
| BC847RAPN v.2 | 20180914 | Product data sheet | - | BC847RAPN v.1 | | | | |
| Modifications: | Package outline draw | Package outline drawing updated: Unit T added | | | | | | |
| BC847RAPN v.1 | 20170607 | Product data sheet | - | - | | | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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